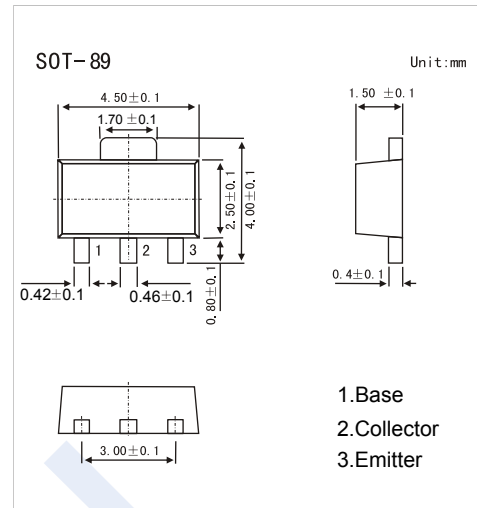


## PNP Transistors

## 2SB956

## ■ Features

- Large collector power dissipation  $P_c$ .
- Low collector to emitter saturation voltage  $V_{CE(sat)}$ .
- Complementary to 2SD1280

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	$V_{CBO}$	-20	V
Collector - Emitter Voltage	$V_{CEO}$	-20	
Emitter - Base Voltage	$V_{EBO}$	-5	
Collector Current - Continuous	$I_C$	-1	A
Collector current -Pulse	$I_{CP}$	-2	
Collector Power Dissipation	$P_C$	1	W
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature range	$T_{stg}$	-55 to 150	

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	$V_{CBO}$	$I_C = -100 \mu\text{A}$ , $I_E = 0$	-20			V
Collector- emitter breakdown voltage	$V_{CEO}$	$I_C = -1 \text{ mA}$ , $I_B = 0$	-20			
Emitter - base breakdown voltage	$V_{EBO}$	$I_E = -100 \mu\text{A}$ , $I_C = 0$	-5			
Collector-base cut-off current	$I_{CBO}$	$V_{CB} = -20\text{V}$ , $I_E = 0$			-1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -5\text{V}$ , $I_C = 0$			-1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -1 \text{ A}$ , $I_B = -50\text{mA}$			-0.5	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500 \text{ mA}$ , $I_B = -50\text{mA}$			-1.2	
DC current gain	$h_{FE(1)}$	$V_{CE} = -2\text{V}$ , $I_C = -500\text{mA}$	130		280	
	$h_{FE(2)}$	$V_{CE} = -2\text{V}$ , $I_C = -1.5 \text{ A}$	50			
Collector output capacitance	$C_{ob}$	$V_{CB} = -6\text{V}$ , $I_E = 0$ , $f = 1\text{MHz}$		40		$\text{pF}$
Transition frequency	$f_T$	$V_{CE} = -6\text{V}$ , $I_E = 50\text{mA}$ , $f = 200\text{MHz}$		200		MHz

■ Classification of  $h_{FE(1)}$ 

Type	2SB956-R	2SB956-S
Range	130-210	180-280
Marking	HR	HS

# PNP Transistors

## 2SB956

### Typical Characteristics

